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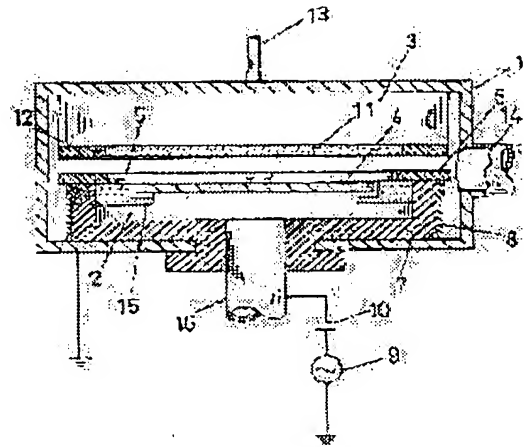
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(54) DRY ETCHING DEVICE

(57)Abstract:

PURPOSE: To provide a dry etching device, which allows a foreign substance to adhere to a wafer only a little even in its long-time use, is easily cleaned, is capable of generating even plasma all over the surface of the wafer and moreover, and is capable of making uniform a selection ratio to a material to be etched and the material of the base of material to be etched within the surface of the wafer.

CONSTITUTION: A sample placing electrode 2 and counter electrode 3 are installed in a vacuum treating chamber 1. The electrode 2 is provided with flat rings 5, which are installed on the outside of a substrate 4 to be treated and consist of a conductive material, and a flat ring 6, which consists of an insulating material, for covering the outer edge parts of the rings 5. Annular flanges 15, which overlap with the edge parts on the side of the rear of the substrate 4, are respectively formed on the insides of the rings 5.



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